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Gate-voltage control of equal-spin Andreev reflection in half-metal/semiconductor/superconductor junctions



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ABSTRACT

With the Blonder–Tinkham–Klapwijk (BTK) approach, we investigate conductance spectrum in Ferromagnet/Semiconductor/Superconductor (FM/Sm/SC) double tunnel junctions where strong Rashba spin–orbit interaction (RSOI) is taken into account in semiconductors. For the half-metal limit, we find that the ingap conductance becomes finite except at zero voltage when inserting a ferromagnetic insulator (FI) at the Sm/SC interface, which means that the appearance of a long-range triplet states in the half-metal. This is because of the emergence of the unconventional equal-spin Andreev reflection (ESAR). When the FI locates at the FM/Sm interface, however, we find the vanishing in-gap conductance due to the absence of the ESAR. Moreover, the non-zero in-gap conductance shows a nonmonotonic dependence on RSOI which can be controlled by applying an external gate voltage. Our results can be used to generate and manipulate the long-range spin triplet correlation in the nascent field of superconducting spintronics.

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1. Introduction

Over the last two decades, the proximity effect in hybrid junctions between the superconductor (SC) and ferromagnet (FM) has received much attention [1–14]. In these junctions, the proximity effect would decay rapidly in the FM since the SC with antiparallel spins and FM with parallel spins are antagonistic [15]. When the magnetization of the FM layer is inhomogeneous, however, the long-range proximity effect is observed due to the triplet pair generation in FM through the spin mixing and spin rotation at the FM/SC interface. For example, long-ranged supercurrents which imply triplet pairing have received considerable theoretical [16–25] and experimental [26–30] attention. Microscopically, the superconducting proximity effect is governed by AR, an electron incident on the interface from the normal state material is phase-coherently reflected a hole of opposite spin and momentum to the incident electron, and vice versa [31]. The spin-triplet pairing effects require the formation of ESAR in which the electrons can be Andreev reflected into holes in the same spin band. There are a large number of works on how to create the ESAR at spin-active FM/SC interface including spin flip process, especially, when FM becomes HM

that only conduction electrons with equal spin can be paired [32, 5,33–37,26,8,38–40].

On the other hand, superconducting spintronics, in analogy with spintronic applications [41,42], have received a boost which aims to use superconductors as active components in spintronic devices [38,43]. One of the topics of the intense research in superconducting spintronics is the effect of spin-orbit (SO) coupling on the charge and spin transports [44–50]. For example, a longrange spin-triplet helix is predicted when the strengths between Rashba and Dresselhaus SO couplings are equal [48]. Jacobsen et al. study the giant triplet proximity effect in π -biased Josephson junctions with spin-orbit coupling [51]. Furthermore, many efforts have been devoted to the effect of the interfacial SO coupling on the charge and spin transport in the non-magnetic junctions [52–54], especially, including superconductors as active components [55–57]. For instance, Bergeret et al. [50] found that a normal metal with SO coupling can be used as the source of longrange triplet proximity effect in FM/SC hybrid structures. More recently, the study of interfacial SO coupling has been extended to the FM/SC junctions [8] where the magnetoanisotropic Andreev reflection is found in the presence of Rashba and Dresselhaus interfacial SO coupling.

In this article, the tunneling conductance spectrum in FM/Sm/SC double tunnel junctions is studied by means of BTK approach [58] where strong RSOI is taken into account in the semiconductors. For the half-metal limit, we find that the in-gap conductance becomes

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finite except at zero voltage when inserting a FI at the Sm/SC interface, which means that the appearance of a long-range triplet states in the half-metal. This is because of the emergence of the unconventional ESAR. When the FI locates at the FM/Sm interface, however, we find the vanishing in-gap conductance due to the absence of the ESAR. Moreover, the non-zero in-gap conductance shows a nonmonotonic dependence on RSOI which can be controlled by applying an external gate voltage. Our results are useful to generate and manipulate the singlet-triplet conversion in the nascent field of superconducting spintronics.

This paper is organized as follows. In Sec. 2 we introduce the model and the mode-matching approach. In Sec. 3 we present our numerical results and discussions. The final Sec. 4 is devoted to a brief summary.

2. Model and formula

We consider a ballistic FM/Sm/SC double-tunnel junctions where strong RSOI is taken into account in semiconductors. FM and SC are separated from the central Sm by two thin FI layers which can induce the spin-filtering effect. The scattering Hamiltonian of two thin FI is defined by the following expression

$$H_{FI}(x) = (U_1 \sigma_0 + U_{M1} \sigma_z) \,\delta(x) + (U_2 \sigma_0 + U_{M2} \sigma_z) \,\delta(x - L) \quad (1)$$

Here $\delta(x)$, $U_{1(2)}$ and $U_{M1(2)}$ are δ function, the barrier amplitude and the exchange potential in the FI [59], respectively.

The effective Hamiltonian (Bogoliubov–de Gennes equation) for quasiparticle states $\Psi(r) = (u_{\uparrow}(r), u_{\downarrow}(r), v_{\uparrow}(r), v_{\downarrow}(r))^{T}$ with energy *E* is given by [60]

$$\begin{pmatrix} H_{+} + H_{FI}(x) & i\sigma_{y}\Delta(x) \\ -i\sigma_{y}\Delta^{*}(x) & -H_{-} - H_{FI}(x) \end{pmatrix} \Psi(\mathbf{r}) = E\Psi(\mathbf{r})$$
(2)

with

$$H_{\pm} = \left[-\frac{\hbar^2}{2} \nabla \left[\frac{1}{m^*(x)} \right] \nabla - E_F(x) \right] \sigma_0 - h_0(x) \sigma_z + \frac{\lambda_{so}(x)}{\hbar} \left(\pm \sigma_x k_y - \sigma_y k_x \right),$$
(3)

with

$$\begin{split} \Delta &(x) = \Delta \Theta \left(x - L \right) \\ m^* \left(x \right) = m \Theta \left(-x \right) + m' \Theta \left(x \right) \Theta \left(L - x \right) + m \Theta \left(x - L \right), \\ E_F \left(x \right) = E_F \Theta \left(-x \right) + \left(E_F - \delta E_c \right) \Theta \left(x \right) \Theta \left(L - x \right) \\ &+ E_F \Theta \left(x - L \right), \\ \lambda_{so} \left(x \right) = \lambda_{so} \Theta \left(x \right) \Theta \left(L - x \right), \\ h_0 \left(x \right) = h_0 \Theta \left(-x \right). \end{split}$$
(4)

Here, Δ is the superconducting pair potential, λ_{so} is the RSOI constant, h_0 is the exchange energy. m(x) and $E_F(x)$ are the positiondependent effective mass and Fermi energy, respectively. The Fermi energy $E_F - \delta E_c$ in the Sm is much smaller than E_F in FM and SC. $\sigma_{x,y,z}$ is the Pauli matrix in the spin space, σ_0 is the unit matrix, $\Theta(x)$ is the step function and $k = (k_x, k_y)$ is the momentum.

Notice that since the Fermi wave vector k_F in the Sm is much smaller than the Fermi wave vector k_F of the left FM and right SC, the incident angle φ_{FM} in the FM has to be virtually zero for transmission according to the translational symmetry along the *y*-axis direction $[k_F^{FM} \sin(\varphi_{FM}) = k_F^{Sm} \sin(\varphi_{Sm}) = k_F^{SC} \sin(\varphi_{SC})]$. Thus, we restrict ourselves to the one-dimensional case in the following.

Consider a beam of spin-up electrons incident from the FM, the general solution of Eq. (2) is of the form aligned

$$\Psi_{I} = \left(e^{iq_{e\uparrow}x} + b_{\uparrow}e^{-iq_{e\uparrow}x}\right)e^{iq_{e\uparrow}x}(1, 0, 0, 0)^{T} + b_{\downarrow}e^{-iq_{e\downarrow}x}(0, 1, 0, 0)^{T} + a_{\uparrow}e^{iq_{h\uparrow}x}(0, 0, 1, 0)^{T} + a_{\downarrow}e^{iq_{h\downarrow}x}(0, 0, 0, 1)^{T},$$
(5)

for x < 0;

$$\Psi_{\rm H} = f_1 e^{ik_{1+x}} (-i, 1, 0, 0)^T + f_2 e^{ik_{1-x}} (i, 1, 0, 0)^T + f_3 e^{-ik_{1+x}} (i, 1, 0, 0)^T + f_4 e^{-ik_{1-x}} (-i, 1, 0, 0)^T + f_5 e^{ik_{2+x}} (0, 0, -i, 1)^T + f_6 e^{ik_{2-x}} (0, 0, i, 1)^T + f_7 e^{-ik_{2+x}} (0, 0, i, 1)^T + f_8 e^{-ik_{2-x}} (0, 0, -i, 1)^T,$$
(6)

for 0 < x < L;

$$\Psi_{\rm III} = c_1 e^{ik_{s+}x} (u, 0, 0, v)^T + c_2 e^{ik_{s+}x} (0, u, -v, 0)^T + c_3 e^{-ik_{s-}x} (v, 0, 0, u)^T + c_4 e^{-ik_{s-}x} (0, v, -u, 0)^T,$$
(7)

for x > L, with

$$q_{e\uparrow(\downarrow)} = \sqrt{\frac{2m}{\hbar^2} (E_F + E \pm h_0)}, \ q_{h\uparrow(\downarrow)} = \sqrt{\frac{2m}{\hbar^2} (E_F - E \pm h_0)},$$

$$k_{1\pm} = \sqrt{\frac{2m'}{\hbar^2} (E_F - \delta E_c + E)} + \left(\frac{m'\lambda_{so}}{\hbar^2}\right)^2 \pm \frac{m'\lambda_{so}}{\hbar^2},$$

$$k_{2\pm} = \sqrt{\frac{2m'}{\hbar^2} (E_F - \delta E_c - E)} + \left(\frac{m'\lambda_{so}}{\hbar^2}\right)^2 \pm \frac{m'\lambda_{so}}{\hbar^2},$$

$$k_{s\pm} = \sqrt{\frac{2m}{\hbar^2} \left(E_F \pm \sqrt{E^2 - \Delta^2}\right)}.$$
(8)

Here, the coherence factors in the superconducting region are u =

$$\sqrt{\frac{1}{2}\left(1+\frac{\sqrt{E^2-\Delta^2}}{E}\right)} \text{ and } \nu = \sqrt{\frac{1}{2}\left(1-\frac{\sqrt{E^2-\Delta^2}}{E}\right)}.$$

The normal reflection b_{\uparrow} , the normal reflection with spin flip b_{\downarrow} , the usual AR a_{\downarrow} , the equal-spin AR a_{\uparrow} can be determined by imposing the following matching conditions at the left and right interfaces

$$\begin{split} \Psi_{\mathrm{I}}(0_{-}) &= \Psi_{\mathrm{II}}(0_{+}), \\ \Psi_{\mathrm{II}}(L_{-}) &= \Psi_{\mathrm{III}}(L_{+}), \\ \hat{v}_{x}\Psi_{\mathrm{II}}(0_{+}) &- \hat{v}_{x}\Psi_{\mathrm{I}}(0_{-}) = \frac{2\hbar k_{F}}{im} \left(Z_{1}\tau_{1} + Z_{2}\tau_{2}\right)\Psi_{\mathrm{I}}(0_{-}), \\ \hat{v}_{x}\Psi_{\mathrm{III}}(L_{+}) &- \hat{v}_{x}\Psi_{\mathrm{II}}(L_{-}) = \frac{2\hbar k_{F}}{im} \left(Z_{3}\tau_{1} + Z_{4}\tau_{2}\right)\Psi_{\mathrm{III}}(L_{+}), \\ \tau_{1} &= \begin{pmatrix} 1 \ 0 \ 0 \ 0 \\ 0 \ 1 \ 0 \ 0 \\ 0 \ 0 \ -1 \ 0 \\ 0 \ 0 \ 0 \ -1 \end{pmatrix}, \\ \tau_{2} &= \begin{pmatrix} -1 \ 0 \ 0 \ 0 \\ 0 \ 1 \ 0 \ 0 \\ 0 \ 0 \ -1 \end{pmatrix}, \end{split}$$
(9)

where $Z_{1(3)} = U_{1(2)}/\hbar v_F$ and $Z_{2(4)} = U_{M1(2)}/\hbar v_F$ are dimensionless parameters describing the charge scattering and the magnetic scattering, respectively, with v_F as the Fermi velocity.

The velocity operator \hat{v}_x in the *x*-direction is given by [45]

$$\hat{\nu}_{x} = \frac{\partial H}{\hbar \partial k}$$

$$= \begin{pmatrix} \frac{\hbar}{im(x)} \frac{\partial}{\partial x} & i \frac{\lambda_{so}(x)}{\hbar} & 0 & 0\\ -i \frac{\lambda_{so}}{\hbar} (x) & \frac{\hbar}{im(x)} \frac{\partial}{\partial x} & 0 & 0\\ 0 & 0 & -\frac{\hbar}{im(x)} \frac{\partial}{\partial x} & -i \frac{\lambda_{so}}{\hbar} (x)\\ 0 & 0 & i \frac{\lambda_{so}}{\hbar} (x) & -\frac{\hbar}{im(x)} \frac{\partial}{\partial x} \end{pmatrix}.$$
(10)

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